

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent Application of)
SATO et al.)
Application Number: To be Assigned)
Filed: Concurrently Herewith)
For: METHOD OF MANUFACTURING AN ACTIVE)
MATRIX SUBSTRATE AND AN IMAGE DISPLAY)
DEVICE USING THE SAME)
ATTORNEY DOCKET NO. HITA.0458)

Honorable Assistant Commissioner
for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Pursuant to 37 C.F.R. §§ 1.56 and 1.97, this Information Disclosure Statement is submitted in the above-identified patent application. A listing of documents to be published on the face of any patent granted from this application is submitted herewith on Form PTO-1449. Any other documents or information submitted for consideration by the Examiner are listed in this paper. A copy of each U.S. and foreign patent, or each publication or portion thereof listed or herein identified, is submitted herewith.

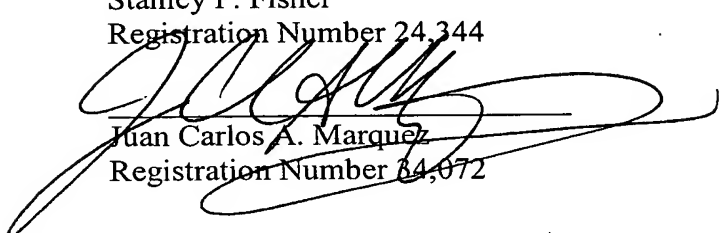
This Information Disclosure Statement is submitted with the initial filing of the application. Accordingly, no fee is due or payable at this time.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

Please charge any additional fees or credit any overpayments in connection with this paper to Deposit Account No. 08-1480.

Respectfully submitted,

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November 14, 2003

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| Form PTO 1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant | ATTY. DOCKET NUMBER HITA-0458 | SERIAL NUMBER To be assigned |
| | APPLICANT SATO et al | |
| | FILING DATE Concurrently herewith | GROUP |

U.S. Patent Documents

| Examiner Initial | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE |
|---------------------|-----------------|------|------|-------|----------|-------------|
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Foreign Patent Documents

| Examiner Initial | DOCUMENT NUMBER | FILING DATE | COUNTRY | CLASS | SUB-CLASS | TRANSLATION | |
|---------------------|-----------------|-------------|---------|-------|-----------|-------------|----|
| | | | | | | YES | NO |
| | 6-140323 | 10/23/92 | Japan | | | Abstract | X |
| | 2001-274088 | 5/28/96 | Japan | | | Abstract | X |
| | 2002-280302 | 3/16/2001 | Japan | | | Abstract | X |
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Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

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|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| | Chang-ho Oh and Masakiyo Matsumura, "Preparation of Position-Controlled Crystal-Silicon Island Arrays by Means of Excimer-Laser Annealing", Jpn. J. Appl. Phys., Vol. 37 (1998) pp. 5474-5479 |
| | Do-Hyun Choi, Kazuhiro Shimizu, Osamu Sugiura and Masakiyo Matsumura, "Drastic Enlargement of Grain Size of Excimer-Laser-Crystallized Polysilicon Films", Jpn. J. Appl. Phys., Vol. 31 (1992) pp. 4545-4549 |
| | Koichi Murakami, Tetsuo Takahashi, Tadamasa Koyanagi, Koichiro Hoh, Yoshio Komiya and Yasuo Tarui, "Thermal Analysis and Experimental Evaluation of Melting Threshold Energy of Si Thin Film Structure in Laser Annealing" Japanese Journal of Applied Physics, Vol. 21, No. 6, June 1982, pp. 879-884 |
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| EXAMINER | DATE CONSIDERED |
| <i>EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant</i> | |